AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A method of semiconductor device fabrication using a semiconductor substrate comprising a lattice-strain relaxed silicon germanium layer and a lattice strained silicon layer formed in this order on ~~of mention onto~~ a silicon substrate or on ~~onto~~ a substrate having a silicon layer on the surface thereof, said method comprising:

an etching step comprising ~~of~~ etching ~~the~~ portions for device isolation regions of said semiconductor substrate so as to form device isolation grooves;

a deposition step comprising ~~of~~ depositing a silicon film on said semiconductor substrate, including in the device isolation grooves formed in said etching step so that the silicon film contacts sidewalls of at least the lattice-strain relaxed silicon germanium layer and sidewalls of the lattice strained silicon layer at least along side(s) of the grooves; ~~and~~

an oxidation step of oxidizing the deposited silicon film; and

forming transistors in respective areas between the grooves in and/or over the lattice strained silicon layer.

2. (Original) A method of semiconductor device fabrication according to claim 1, wherein in said deposition step, a silicon film of 5 through 10 nm is deposited.

3. (Original) A method of semiconductor device fabrication according to claim 2, wherein in said oxidation step, said deposited silicon film is oxidized completely.

4. (Original) A method of semiconductor device fabrication according to claim 3, further comprising the step of depositing a protective film for protecting portions for device activity regions onto the surface of said semiconductor substrate before said etching step.

5. (Original) A method of semiconductor device fabrication according to claim 1, wherein in said oxidation step, said deposited silicon film is oxidized completely.

6. (Original) A method of semiconductor device fabrication according to claim 5, wherein in said deposition step, a silicon film of 5 through 10 nm is deposited.

7. (Original) A method of semiconductor device fabrication according to claim 6, further comprising the step of depositing a protective film for protecting portions for device activity regions onto the surface of said semiconductor substrate before said etching step.

8. (Original) A method of semiconductor device fabrication according to claim 1, further comprising the step of depositing a protective film for protecting portions for device activity regions onto the surface of said semiconductor substrate before said etching step.

9. (Original) A method of semiconductor device fabrication according to claim 8, wherein in said deposition step, a silicon film of 5 through 10 nm is deposited.

10. (Canceled)

11. (Currently amended) A method of semiconductor device fabrication using a semiconductor substrate comprising a lattice-strain relaxed silicon germanium layer, one or more semiconductor layers, and a lattice strained silicon layer formed in this order on ~~of mention onto~~ a silicon substrate or on ~~onto~~ a substrate having a silicon layer on the surface thereof, said method comprising:

an etching step comprising ~~of~~ etching ~~the~~ portions for device isolation regions of said semiconductor substrate so as to form device isolation grooves;

a deposition step comprising ~~of~~ depositing a silicon film on said semiconductor substrate, including in the device isolation grooves formed in said etching step so that the silicon film contacts sidewalls of at least the lattice-strain relaxed silicon germanium layer and sidewalls of the lattice strained silicon layer along side(s) of the grooves; and

an oxidation step of oxidizing the deposited silicon film.

12. (Original) A method of semiconductor device fabrication according to claim 11, wherein in said deposition step, a silicon film of 5 through 10 nm is deposited.

13. (Original) A method of semiconductor device fabrication according to claim 12, wherein in said oxidation step, said deposited silicon film is oxidized completely.

14. (Original) A method of semiconductor device fabrication according to claim 13, further comprising the step of depositing a protective film for protecting portions for device activity regions onto the surface of said semiconductor substrate before said etching step.

15. (Original) A method of semiconductor device fabrication according to claim 11, wherein in said oxidation step, said deposited silicon film is oxidized completely.

16. (Original) A method of semiconductor device fabrication according to claim 15, wherein in said deposition step, a silicon film of 5 through 10 nm is deposited.

17. (Original) A method of semiconductor device fabrication according to claim 16, further comprising the step of depositing a protective film for protecting portions for device activity regions onto the surface of said semiconductor substrate before said etching step.

18. (Original) A method of semiconductor device fabrication according to claim 11, further comprising the step of depositing a protective film for protecting portions for device activity regions onto the surface of said semiconductor substrate before said etching step.

19. (Original) A method of semiconductor device fabrication according to claim 18, wherein in said deposition step, a silicon film of 5 through 10 nm is deposited.

20. (Original) A method of semiconductor device fabrication according to claim 19, wherein in said oxidation step, said deposited silicon film is oxidized completely.